

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1-27. (Canceled).

28. (Previously presented): A method of manufacturing a semiconductor device comprising the steps of:
forming an amorphous semiconductor film over a substrate;
irradiating the amorphous semiconductor film with a third harmonic of a continuous wave laser comprising Nd to crystallize the amorphous semiconductor film; and
patterning the crystallized semiconductor film to form an active layer including at least a channel formation region.

29. (Previously presented): The method according to claim 28 wherein said amorphous semiconductor film comprises amorphous silicon.

30. (Previously presented): The method according to claim 28 wherein said continuous wave laser comprising Nd is an Nd:YAG laser.

31-33. (Canceled).

34. (Previously presented): A method of manufacturing a semiconductor device, the method comprising:
forming an amorphous semiconductor film over a substrate;
irradiating the amorphous semiconductor film with a third harmonic of a laser comprising Nd to crystallize the amorphous semiconductor film; and

patterning the crystallized semiconductor film to form an active layer including at least a channel formation region.

35. (Previously presented): The method according to claim 34 wherein said amorphous semiconductor film comprises amorphous silicon.

36. (Previously presented): The method according to claim 34 wherein said laser comprising Nd is a Nd:YAG laser.

37-42. (Canceled).